

Silicon NPN Power Transistors

2SC3264

DESCRIPTION

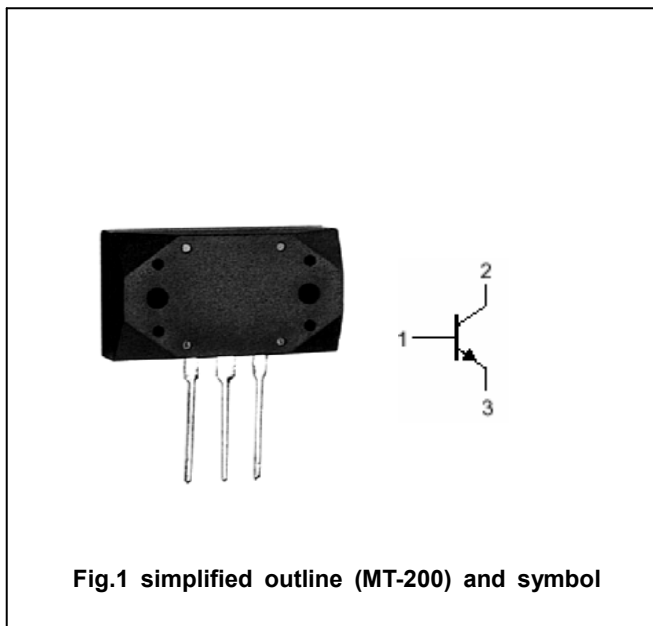
- With MT-200 package
- Complement to type 2SA1295

APPLICATIONS

- Audio and general purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	230	V
V _{CEO}	Collector-emitter voltage	Open base	230	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		17	A
I _B	Base current		5	A
P _C	Collector power dissipation	T _C =25°C	200	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=25mA ; I_B=0$	230			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A ; I_B=0.5A$			2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=230V ; I_E=0$			100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			100	μA
h_{FE}	DC current gain	$I_C=5A ; V_{CE}=4V$	50		140	
C_{ob}	Output capacitance	$I_E=0 ; V_{CB}=10V ; f=1MHz$		250		pF
f_T	Transition frequency	$I_E=-2A ; V_{CE}=12V$		60		MHz

Switching times

t_{on}	Turn-on time	$I_C=5A ; R_L=12\Omega$ $I_{B1}=-I_{B2}=0.5A$ $V_{CC}=60V$		0.30		μs
t_s	Storage time			2.40		μs
t_f	Fall time			0.50		μs

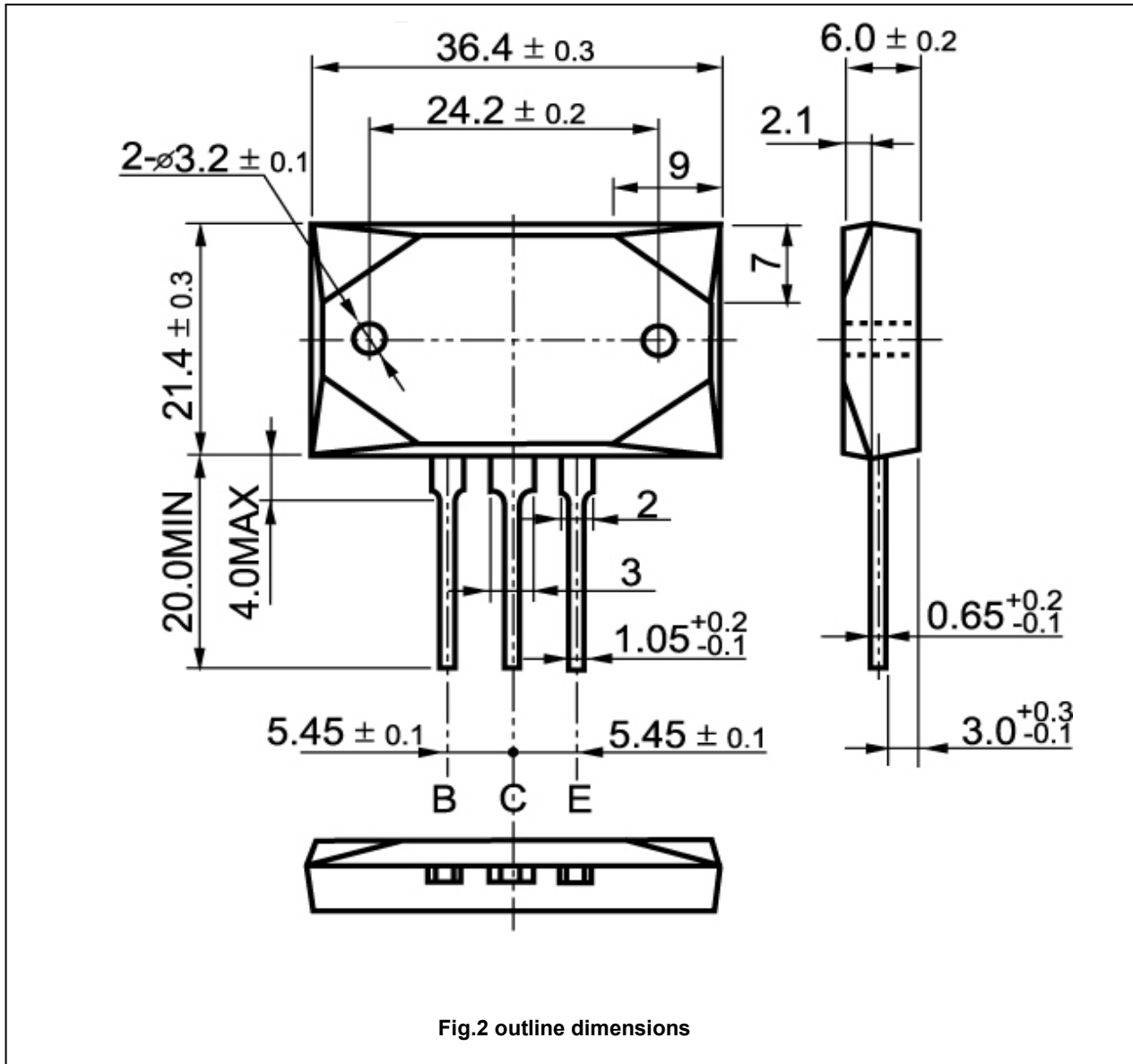
◆ h_{FE} classifications

O	Y
50-100	70-140

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PACKAGE OUTLINE



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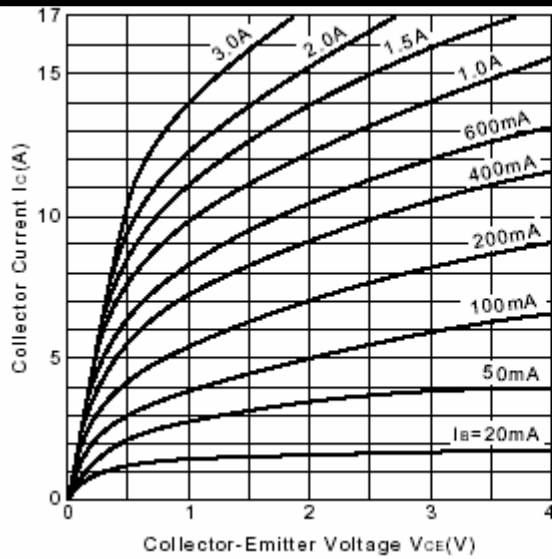


Fig.3 Static Characteristic

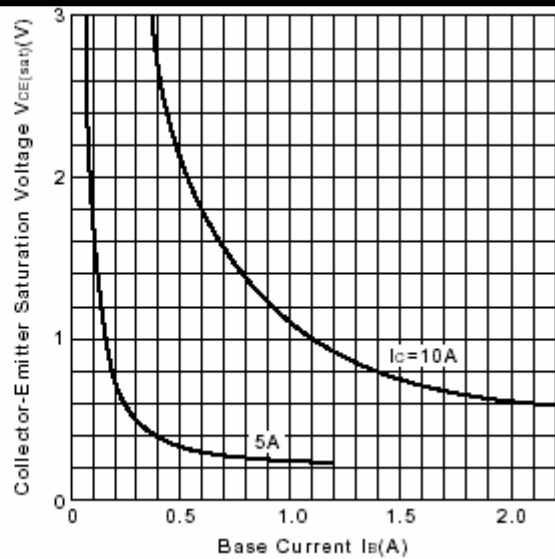


Fig.4 $V_{CE(sat)}-I_B$

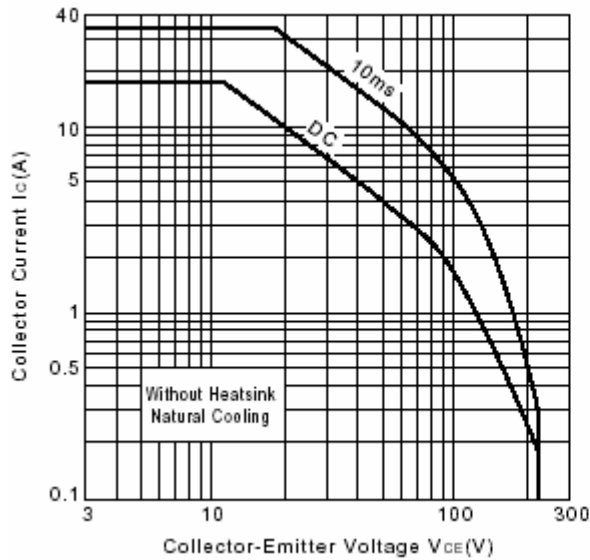


Fig.5 Safe Operating Area

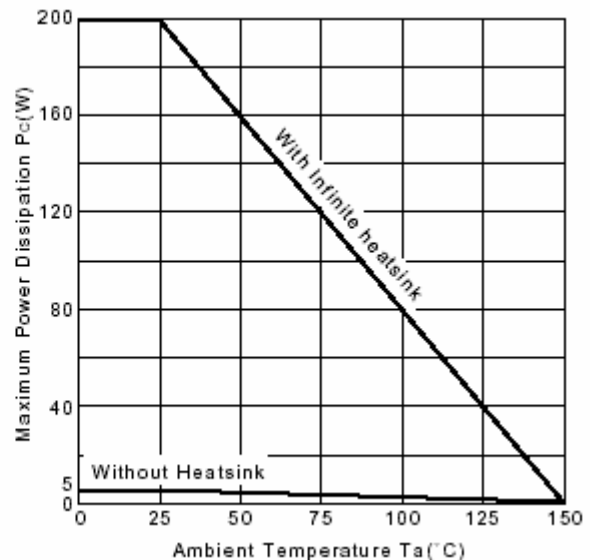


Fig.6 Power Derating

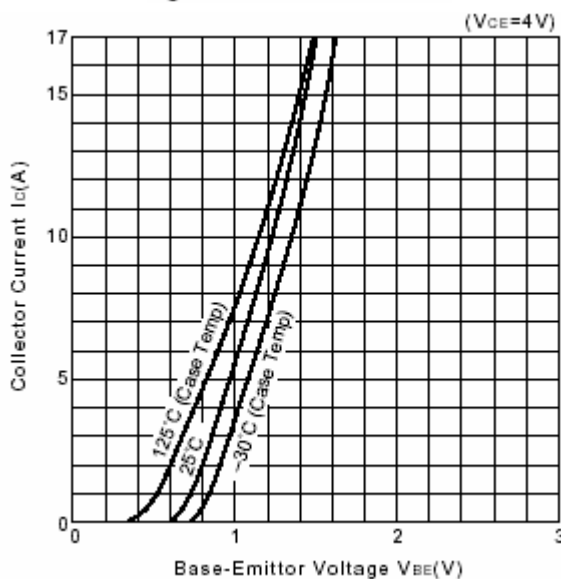


Fig.7 I_C-V_{BE}

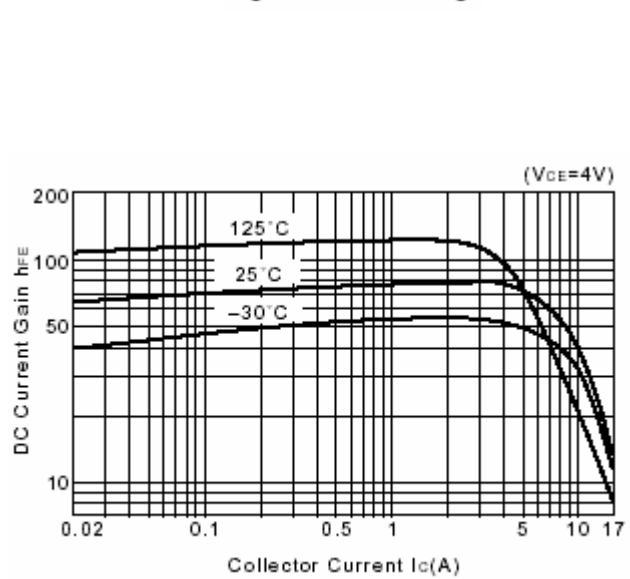


Fig.8 DC current Gain